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06EC56

**Fifth Semester B.E. Degree Examination, June/July 2011**  
**Fundamentals of CMOS VLSI**

Time: 3 hrs.

Max. Marks:100

**Note: Answer any FIVE full questions, selecting at least TWO questions from each part.**

**PART – A**

- 1 a. Describe in detail step-by-step procedure of P-well CMOS fabrication. (08 Marks)  
 b. Explain the transfer plot of CMOS inverter with necessary expression for  $V_{out}$  in each region. (08 Marks)  
 c. Write a note on transmission gate. (04 Marks)
- 2 a. Draw circuit diagram and stick diagrams of two input NOR gate using CMOS logic use standard colour/monochrome codes. (08 Marks)  
 b. Explain  $\lambda$  based design rules applicable to MOS layers and transistors. (08 Marks)  
 c. Write a note on Double metal MOS process rules for contact cut. (04 Marks)
- 3 Explain the following logic structures with their salient features:  
 a. BiCMOS logic    b. Pseudo-nMOS logic    c. Pass transistor logic    d. C<sup>2</sup>MOS logic. (20 Marks)
- 4 a. Define sheet resistance, standard unit of capacitance and delay unit of time. (06 Marks)  
 b. Explain cascaded inverters to drive large capacitive loads. Obtain an equation to find number of stages. (08 Marks)  
 c. Discuss the following in scaling of MOS circuits:  
     i) Limit of miniaturization    ii) Limits of interconnect and contact resistance. (06 Marks)

**PART – B**

- 5 a. Explain the structured design of a parity generator with necessary blocks and stick diagram. (10 Marks)  
 b. Explain domino CMOS logic with neat circuit. (10 Marks)
- 6 a. List and explain the general considerations to be considered in Digital system design. (06 Marks)  
 b. Explain the design of datapath in 4-bit arithmetic processor with floor plan for 4-bit datapath. (10 Marks)  
 c. Write MOS switch implementation of 4x4 crossbar switch. (04 Marks)
- 7 a. What are timing considerations in system design? (06 Marks)  
 b. Draw one-transistor dynamic memory cell circuit arrangement. What is the significance of creating capacitor by using a polysilicon plate over the diffusion area? (08 Marks)  
 c. Explain six transistor static CMOS memory cell arrangement. (06 Marks)
- 8 a. Discuss the requirements of I/O pads in a chip. (05 Marks)  
 b. Explain the sensitized path based testing applied to combinational logic as an example. (10 Marks)  
 c. Write a note on scan design technique. (05 Marks)

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Important Note : 1. On completing your answers, carefully draw diagonal cross lines on the remaining blank pages. 2. Any revealing of identification, appeal to evaluator and/or equations written eg. 42+8 = 50, will be treated as malpractice.

